Vishay Semiconductors

COMPLIANT

HALOGEN

## Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS							
I <sub>T(AV)</sub>	10 A						
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V						
$V_{TM}$	1.4 V						
I <sub>GT</sub>	60 mA						
T <sub>J</sub>	-40 °C to 125 °C						
Package	D <sup>2</sup> PAK (TO-263AB)						
Circuit configuration	Single SCR						

#### **FEATURES**

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

 Designed and qualified according JEDEC®-JESD 47

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **APPLICATIONS**

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-16TTS..S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 µm) copper	2.5	3.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	6.3	9.5	A						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	14.0	18.5							

#### Note

• T<sub>A</sub> = 55 °C, T<sub>J</sub> = 125 °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	10	A					
I <sub>RMS</sub>		16	^					
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V					
I <sub>TSM</sub>		200	Α					
$V_{T}$	10 A, T <sub>J</sub> = 25 °C	1.4	V					
dV/dt		500	V/µs					
dI/dt		150	A/μs					
T <sub>J</sub>		-40 to +125	°C					

VOLTAGE RATINGS									
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> AT 125 °C mA						
VS-16TTS08S-M3	800	800	10						
VS-16TTS12S-M3	1200	1200	10						



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ABSOLUTE MAXIMUM RATINGS		T.		1		1	
PARAMETER	SYMBOL		TEST CONDITIONS	VAL	UNITS		
ADAMETER	OTMEGE		.ES. SCADITIONS			0.11.10	
Maximum average on-state current	I <sub>T(AV)</sub>	$T_{\rm C} = 98  {}^{\circ}{\rm C},  {}^{2}$	80° conduction, half sine wave	1			
Maximum RMS on-state current	I <sub>RMS</sub>			1	6	Α	
Maximum peak, one-cycle,		10 ms sine p	ulse, rated V <sub>RRM</sub> applied	1	70	_ ^	
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine p	ulse, no voltage reapplied	20	00	1	
Maximum 12t for fusing	I <sup>2</sup> t	10 ms sine p	ulse, rated V <sub>RRM</sub> applied	144		A2-	
Maximum I <sup>2</sup> t for fusing	1-1	10 ms sine p	200		- A <sup>2</sup> s		
Maximum I <sup>2</sup> √t for fusing	I²√t	t = 0.1 ms to	10 ms, no voltage reapplied	2000		A²√s	
Maximum on-state voltage drop	$V_{TM}$	10 A, T <sub>J</sub> = 25	5 °C	1.4		V	
On-state slope resistance	r <sub>t</sub>	T 105 %		24.0		mΩ	
Threshold voltage	V <sub>T(TO)</sub>	IJ = 125 °C	T <sub>J</sub> = 125 °C		.1	V	
Maximum various and direct lockers current	1 /1	T <sub>J</sub> = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DRM}$	0.5			
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	T <sub>J</sub> = 125 °C		1	0		
Holding current	I <sub>H</sub>	Anode supply = 6 V, resistive load, initial $I_T$ = 1 A, $T_J$ = 25 °C		-	150	mA	
Maximum latching current	ΙL	Anode suppl	200		1		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max. linear to 80 % $V_{DRM} = R_g - k = open$			500		
Maximum rate of rise of turned-on current	dl/dt				150		

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P <sub>GM</sub>		8.0	W				
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV				
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α				
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	90	mA				
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	60					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	35					
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	3.0					
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V				
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V				
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = Poted value	0.25					
Maximum DC gate current not to trigger	I <sub>GD</sub>	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = Rated value	2.0	mA				

SWITCHING								
PARAMETER SYMBOL TEST CONDITIONS VALUES UN								
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9					
Typical reverse recovery time	t <sub>rr</sub>	T <sub>.I</sub> = 125 °C	4	μs				
Typical turn-off time	t <sub>q</sub>	1j = 125	110					

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THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	METER SYMBOL TEST CONDITIONS								
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation	1.3	°C/W					
Typical thermal resistance, junction to ambient	R <sub>thJA</sub>	PCB mount (1)	40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	oz.					
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	16TTS08S						
ividi kilig device		Case style D-FAR (10-203AB)	16TTS12S						

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

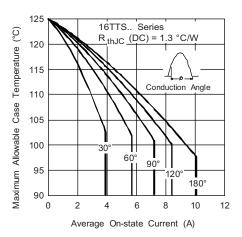


Fig. 1 - Current Rating Characteristics

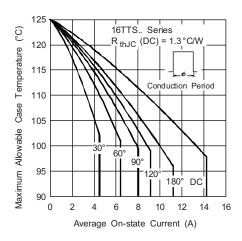


Fig. 2 - Current Rating Characteristics

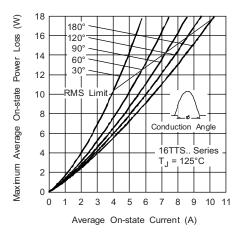


Fig. 3 - On-State Power Loss Characteristics

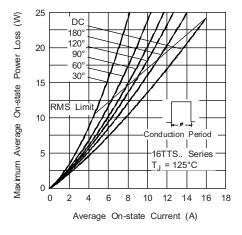


Fig. 4 - On-State Power Loss Characteristics

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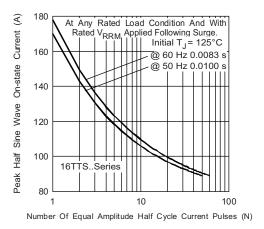


Fig. 5 - Maximum Non-Repetitive Surge Current

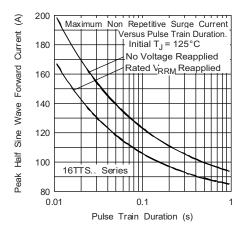


Fig. 6 - Maximum Non-Repetitive Surge Current

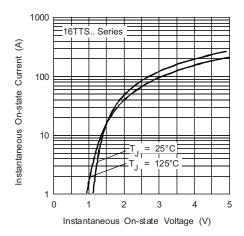


Fig. 7 - On-State Voltage Drop Characteristics

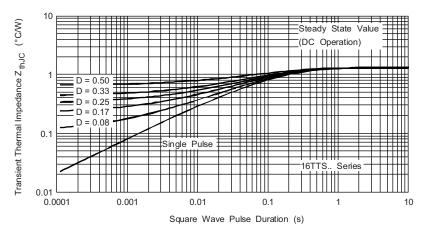


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

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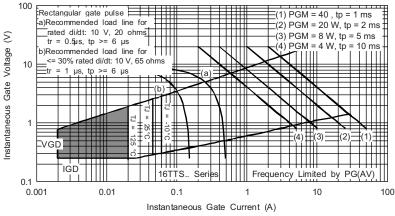
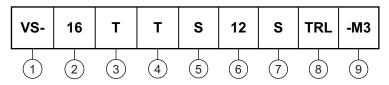


Fig. 9 - Gate Characteristics

### **ORDERING INFORMATION TABLE**

#### Device code



- 1 Vishay Semiconductors product
- 2 Current rating
- Circuit configuration:
  - T = single thyristor
- 4 Package:
  - $T = D^2PAK (TO-263AB)$
- 5 Type of silicon:
  - S = standard recovery rectifier
- 08 = 800 V 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-16TTS08S-M3	50	Antistatic plastic tubes							
VS-16TTS08STRL-M3	800	13" diameter plastic tape and reel							
VS-16TTS08STRR-M3	800	13" diameter plastic tape and reel							
VS-16TTS12S-M3	50	Antistatic plastic tubes							
VS-16TTS12STRL-M3	800	13" diameter plastic tape and reel							
VS-16TTS12STRR-M3	800	13" diameter plastic tape and reel							

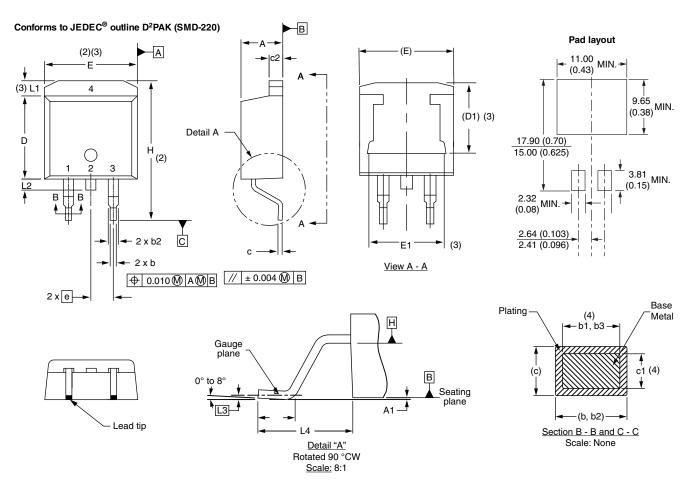
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				
SPICE model	www.vishay.com/doc?96772				



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### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

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